Dynamically reconfigurable optical amplification element

IN RE APPLICATION OF: Edward H. Sargent

09/988,030 SERIAL NO: FILED: November 16, 2001

GAU: **EXAMINER:** 

2874

Not yet assigned

## INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.9

COMMISSIONER FOR PATENTS WASHINGTON, D.C. 20231

SIR:

FOR:

Applicant(s) wish to disclose the following information.

#### REFERENCES

$\boxtimes$	The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies
	of the listed references are attached, where required, as are either statements of relevancy or any readily
	available English translations of pertinent portions of any non-English language references.

A check is attached in the amount required under 37 CFR §1.17(p).

#### RELATED CASES

Attached is a copy of applicant's pending application(s) or issued patent(s) which may be related to the present application. These documents are listed on form PTO-1449, also attached.

A check is attached in the amount required under 37 CFR §1.17(p).

#### **CERTIFICATION**

Each item of information contained in this information disclosure statement was cited for the first time in any communication from a foreign patent office in any counterpart foreign application not more than three months prior to the filing of this statement.

 $\Box$ No item of information contained in this information disclosure statement was cited for the first time in any communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

П This Information Disclosure Statement is being filed within three months of the filing date of the subject patent application.

 $\boxtimes$ This Information Disclosure Statement is being filed before the mailing date of a first Office Action on the merits.

#### **PETITION**

 $\boxtimes$ 

Applicant(s) hereby request consideration of the attached information. A check is attached in the amount of the Petition fee required under 37 CFR §1.17(i)(1).

### DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 23-2185. A duplicate copy of this sheet is enclosed.

Respectfully Submitted,

BLANK ROME COMISKY & MCCAULEY LLP

THE FARRAGUT BUILDING SUITE 1000 900 17<sup>TH</sup> STREET, NW WASHINGTON, DC 20006 TEL (202) 530-7400 FAX (202) 463-6915

27557

Date: April 12, 2002

David J. Edmondson Attorney of Record Registration No. 35,126

O8/01

Form	PTO	1449
44 4 - 41	r - 41	

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFISE RADEMA

NTY. DOCKET NO. 115354.00104 SERIAL NO. . 09/988.030

# LIST OF REFERENCES CITED BY APPLICANT

APPLICANT Edward H. Sargent

FILING DATE November 16, 2001 GROUP 2874

U.S. PATENT DOCUMENTS SUB **FILING DATE CLASS** EXAMINER DOC. NUMBER DATE NAME CLASS IF APPROPRIATE INITIAL AA 6,027,989 Feb. 22, 2000 Poole et al. AB 5,915,165 Jun. 22, 1999 Sun et al. AC Mar. 16, 1999 Bhat 5.882,951 AD Beernink et al. 5.843,802 Dec. 1, 1998 ΑE **Bhat** 5,771,256 Jun. 23, 1998 AF Thornton et al. Jun. 16, 1998 5,766,981 AG Beernink et al. 5,708,674 Jan. 13, 1998 AH Emery et al. 5,707,890 Jan. 13, 1998 Al Paoli et al. 5,608,753 Mar. 4, 1997 AJ Paoli et al. 5,574,745 Nov. 12, 1996 AK 5,539,763 Jul. 23, 1996 Takemi et al. AL Oct. 3, 1995 Paoli et al. 5,455,429 AM 5,425,043 Jun. 13, 1995 Holonyak, Jr. et al. AN 5,395,793 Mar. 7, 1995 Charbonneau et al. ΑO 5,353,295 Oct. 4, 1994 Holonyak, Jr. et al. AP D'Asaro et al. 5,298,454 Mar. 29, 1994 AQ Holonyak, Jr. et al. 4,871,690 Oct. 3, 1989 AR Harder et al. 4,805,179 Feb. 14, 1989 AS FOREIGN PATENT DOCUMENTS COUNTRY TRANSLATION DOC. NUMBER DATE NO YES ΑĪ ΑŬ ΑV OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.) Journal of Crystal Growth (2000), "Growth of novel InP-based materials by He-plasma-assisted epitaxy," Authors: Pinkney et al.; Pages 237-241 J. Vac. Sci. Technol. A 16(2), Mar/Apr 1998, "Characterization of annealed high-resistivity InP grown by He-plasmaassisted epitaxy," Authors: Pinkney et al.; Pages 772-775 J. Vac. Sci. Technol. A 16(2), Mar/Apr 1998, "Quantum well intermixing in material systems for 1.5 μm (invited),"

Examiner Date Considered

grown GaAs layers," Authors: Tsang et al.; Pages 664-670

Authors: Marsh et al.; Pages 810-816

et al.; Pages 1016-1018

BB

BC

BD

Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

IEEE Photonics Technology Letters, Vol. 8, No. 9, September 1996, "10 Gb/s Wavelength Conversion with Integrated

J. Appl. Phys. 79(2), 15 January 1996, "Compositional disordering of InGaAs/GaAs heterostructures by low-temperature-

IEEE Photonics Technology Letters, Vol. 7, No. 9, September 1995, "Monolithic Integration of InGaAsP-InP Stratined-

Layer Distributed Feedback Laser and External Modulator by Selective Quantum-Well Interdiffusion," Authors: Ramdane

Multiquantum-Well-Based 3-Port Mach-Zehnder Interferometer," Authors: Idler et al.; Pages 1163-1165

Quantum Well Intermixing Caused By Non-Stoichiometric INP," Authors: Haysom et al.; Pages 56-59